

10/707,878

FIS920030317US1

In the claims:

1. (Currently amended) A method of forming a layer of silicon on a surface of a workpiece comprising the steps of:  
heating said workpiece on a substrate in a vacuum chamber;  
depositing a layer of silicon on a surface of said workpiece ~~reacting at least two reactants to form said silicon;~~  
in which said step of heating comprises supplying more than half of a total heating power to a lower surface of said workpiece, whereby said workpiece is maintained at a deposition temperature greater than a crystallization temperature of silicon during the depositing of the layer of silicon.
2. (Original) A method according to claim 1, in which said heating power is supplied by an upper set of lamps disposed above said workpiece and a lower set of lamps disposed below said substrate.
3. (Original) A method according to claim 2, in which approximately eighty percent of said heating power is supplied to said lower set of lamps.
4. (Original) A method according to claim 1, in which said substrate is maintained at a temperature of greater than 690 °C.
5. (Original) A method according to claim 2, in which said substrate is maintained at a temperature of greater than 690 °C.
6. (Original) A method according to claim 3, in which said substrate is maintained at a temperature of greater than 690 °C.
7. (Original) A method according to claim 4, in which said substrate is maintained at a temperature of less than 710 °C.

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8. (Original) A method according to claim 5, in which said substrate is maintained at a temperature of less than 710°C.
9. (Original) A method according to claim 6, in which said substrate is maintained at a temperature of less than 710°C.
10. (Original) A method according to claim 1, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
11. (Original) A method according to claim 2, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
12. (Original) A method according to claim 3, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
13. (Original) A method according to claim 4, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
14. (Original) A method according to claim 5, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
15. (Original) A method according to claim 6, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.
16. (Original) A method according to claim 7, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.

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17. (Original) A method according to claim 8, in which said step of heating comprises supplying more than 75% of a total heating power to a lower surface of said workpiece.

18. to 20. (Withdrawn)